

2. (Amended) A semiconductor device, comprising:
 a semiconductor film having a source region and a drain region;
 a gate insulating film formed on at least part of the semiconductor film; and
 a gate electrode formed on the gate insulating film, a width of the gate electrode being smaller than a width of the semiconductor film.

3. (Twice Amended) The semiconductor device according to Claim 1,
 further comprising a sub gate electrode connected to the gate electrode.

4. (Amended) The semiconductor device according to Claim 3,
 the sub gate electrode being disposed on the gate electrode.

5. (Twice Amended) The semiconductor device according to Claim 3,
 the sub gate electrode being disposed so as to cover at least one end of the semiconductor film.

6. (Amended) A semiconductor device, comprising:
 a semiconductor film including ends that include regions formed of an intrinsic semiconductor which is not doped with dopant;
 a gate insulating film formed on at least part of the semiconductor film; and
 a gate electrode formed on the gate insulating film.

7. (Amended) A semiconductor device, comprising:
 a semiconductor film;
 a gate insulating film formed on at least part of the semiconductor film; and
 a gate electrode formed on the gate insulating film, the semiconductor film including a region formed of an intrinsic semiconductor which is not doped with dopant, the region extending past the gate electrode.

8. (Amended) A semiconductor device, comprising:
 a semiconductor film having a source region and a drain region;
 a gate insulating film formed on at least part of the semiconductor film; and

a gate electrode formed on the gate insulating film, the semiconductor film including a region formed of an intrinsic semiconductor which is not doped with dopant, the region extending toward at least one of the source region and the drain region from the gate electrode.

9. (Amended) A semiconductor device, comprising:

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a semiconductor film having a source region and a drain region, the semiconductor film including a plurality of regions formed of an intrinsic semiconductor which is not doped with dopant;

a gate insulating film formed on at least part of the semiconductor film;

a gate electrode formed on the gate insulating film; and

the regions extending toward at least one of the source region and the drain

region from the gate electrode.

10. (Twice Amended) The semiconductor device according to Claim 1,
B6 Sub C1
the semiconductor film being formed on an insulating layer.

11. (Twice Amended) A circuit board, comprising:

the semiconductor device according to Claim 1; and

wires that supply at least one of signals and electric power to the

semiconductor device.

12. (Amended) An electro-optical device, comprising:

B7 Sub C1
the circuit board according to Claim 11;

a first electrode formed above the circuit board; and

an electro-optical element formed above the first electrode.